AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

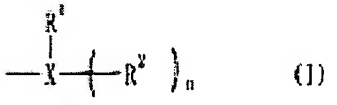
1. (currently amended) A material for chemical vapor deposition comprising a precursor composed of a metal compound, wherein impurities generated as a result of decomposition of the precursor are present as particles, and the material contains 100 or less of the particles ~~having~~ with a size of 0.5 μm or more in 1 ml, in particle measurement by a light scattering submerged particle detector in a liquid phase.

2. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the number of particles having a size of 0.3 μm or more is 100 or less in 1 ml, in particle measurement by a light scattering submerged particle detector.

3. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the number of particles having a size of 0.2 μm or more is 1000 or less in 1 ml, in particle measurement by a light scattering submerged particle detector.

4. (previously presented) The material for chemical vapor deposition according to claim 3, wherein the number of particles having a size of 0.2 μm or more is 100 or less in 1 ml, in particle measurement by a light scattering submerged particle detector.

5. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (I) shown below bonds to the metal atom:



(I)

wherein X represents an oxygen atom or a nitrogen atom; n represents 0 when X is an oxygen atom or n represents 1 when X is a nitrogen atom; R^1 represents an organic group having 1 to 10 carbon atoms; and R^2 represents a hydrogen atom or an organic group having 1 to 10 carbon atoms.

6. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the precursor is composed of a metal compound having a structure wherein the group represented by general formula (II) shown below bonds to the metal atom:

(II)

wherein R^3 represents an alkyl group having 1 to 8 carbon atoms or a cyclopentadienyl group having 1 to 10 carbon atoms.

7. (previously presented) The material for chemical vapor deposition according to claim 1, wherein the metal compound is selected from an aluminum compound, a titanium compound, a zirconium compound, a hafnium compound, a tantalum compound, and a niobium compound.

8. (original) The material for chemical vapor deposition according to claim 7, wherein the metal compound is a hafnium compound.

9. (previously presented) The material for chemical vapor deposition according to claim 1, which is delivered or fed in a liquid phase.

10. (canceled)

11. (previously presented) The material for chemical vapor deposition according to claim 2, wherein the number of particles having a size of 0.2 μm or more is 1000 or less in 1 ml, in particle measurement by a light scattering submerged particle detector.